

**AMENDMENT TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-24 (canceled)

25. (Previously presented): The circuit arrangement according to Claim 29, wherein the flip-flop has two inverters formed from the storage transistors.

26. (Withdrawn): The circuit arrangement according to Claim 29, wherein the first power switch transistor is a common power switch transistor provided for the flip-flop and for at least one additional flip-flop.

27. (Previously presented): The circuit arrangement according to one of Claim 29, wherein the thickness of a gate insulating layer of the storage transistors and/or of the first power switch transistor is greater than the thickness of the gate insulating layer of the switching transistors.

28. (Previously presented): The circuit arrangement according to Claim 29, wherein a channel width of the storage transistors and/or of the first power switch transistor is less than the channel width of the switching transistors.

29. (Currently Amended): A circuit arrangement comprising:  
a flip-flop having a plurality of storage transistors with a threshold voltage of a first value;  
a first power switch transistor having a threshold voltage of a second value, wherein an application of a predetermined electrical potential to the first power switch transistor's gate terminal brings the circuit arrangement to an operating state in which if at least one supply voltage is





42. (Previously presented): The circuit arrangement according to Claim 41, wherein the test transistors have a gate insulating layer having a thickness greater than a thickness of the gate insulating layer of the switching transistors.

43. (Previously presented): The circuit arrangement according to Claim 41, wherein the test transistors have a gate insulating layer having a thickness greater than a thickness of a gate insulating layer of the pulse generator transistors.

44. (Previously presented): The circuit arrangement according to Claim 41, wherein the test transistors have a gate insulating layer having a thickness greater than a thickness of a gate insulating layer of the logic transistors.

45. (Previously presented): The circuit arrangement according to Claim 29, further comprising one or more protection transistors having a threshold voltage of a fourth value and located between the flip-flop and the switching transistors, wherein the protection transistors selectively couple or decouple the flip-flop and the switching transistors, and the magnitude of the fourth value is greater than the magnitude of the third value.

46. (Previously presented): The circuit arrangement according to Claim 45, wherein the protection transistors have a gate insulating layer having a thickness greater than a thickness of the gate insulating layer of the switching transistors.

47. (Previously presented): The circuit arrangement according to Claim 34, further comprising one or more protection transistors having a threshold voltage of a fifth value and located between the flip-flop and the switching transistors, wherein the protection transistors selectively couple or decouple the flip-flop and the switching transistors, and the magnitude of the fifth value is greater than the magnitude of the third value, and

wherein the protection transistors have a gate insulating layer having a thickness greater than a thickness of the gate insulating layer of the pulse generator transistors.



at least one additional flip-flop having a plurality of storage transistors with a threshold voltage of the first value;

a first power switch transistor having a threshold voltage of a second value, wherein an application of a predetermined electrical potential to the first power switch transistor's gate terminal brings the circuit arrangement to an operating state in which if at least one supply voltage is switched off, electric charge carriers contained in the circuit arrangement are prevented from discharging from the circuit arrangement; and

a plurality of switching transistors, having a threshold voltage of a third value, provided between the flip-flop and the first power switch transistor, for coupling a flip-flop input signal into the flip-flop;

wherein the magnitude of the first and/or the second value is greater than the magnitude of the third value;

a pulse generator circuit that generates a flip-flop input signal from an input signal and from a clock signal and is coupled to the first power switch transistor and to the switching transistors; and

wherein the first power switch transistor is a common power switch transistor provided for the flip-flop and for the at least one additional flip-flop.

52. (New) A circuit arrangement comprising:

a flip-flop having a plurality of storage transistors with a threshold voltage of a first value;

a first power switch transistor having a threshold voltage of a second value, wherein an application of a predetermined electrical potential to the first power switch transistor's gate terminal brings the circuit arrangement to an operating state in which if at least one supply voltage is



a plurality of switching transistors, having a threshold voltage of a third value, provided between the flip-flop and the first power switch transistor, for coupling a flip-flop input signal into the flip-flop wherein at least one of the terminals of the switching transistors has a defined electrical potential in the operating state;

wherein the magnitude of the first and/or the second value is greater than the magnitude of the third value; and

at least one second power switch transistor, which is coupled to at least a portion of the switching transistors such that, in an operating state of the circuit arrangement in which at least one supply voltage of the circuit arrangement is switched off, a source/drain terminal of each of the switching transistors coupled to the at least one third power switch transistor has a defined electrical potential.